

MICROWAVE LINEAR POWER TRANSISTORS

NPN transistors for use in a common-emitter class-A linear power amplifier up to 4 GHz.

Diffused emitter ballasting resistors, self-aligned process entirely ion implanted and gold metallization ensure an optimum temperature profile, excellent performance and reliability.

The LBE2003S and LBE2009S have a metal ceramic studless envelope.

The LCE2009S has a metal ceramic capstan envelope.

The LBE2009SA and LCE2009SA are tested by sampling on RF parameters.

QUICK REFERENCE DATA

RF performance up to $T_{mb} = 25^{\circ}\text{C}$ in a common-emitter class-A circuit

type number	mode of operation	f GHz	V _{CE} V	I _C mA	P _{L1} mW	G _{po} dB	z _i Ω	z _L Ω
LBE2003S	CW; linear amplifier	2	18	30	≥ 200	≥ 10	$6.2 + j30$	$17.5 + j7$
LBE/LCE2009S	CW; linear amplifier	2	18	110	≥ 700	≥ 9	$7.5 + j15$	$17.5 + j39$

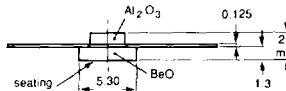
MECHANICAL DATA

Fig.1a LBE2003S and LBE2009S.

FO-45

Pinning:

- 1 = collector
- 2 = emitter
- 3 = base
- 4 = emitter



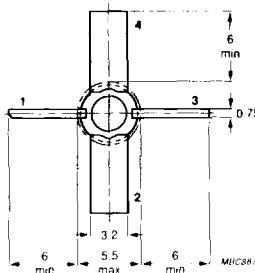
Dimensions in mm

Marking code:

407 = LBE2003S

409 = LBE2009S

445 = LBE2009SA



WARNING

Product and environmental safety — toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions.

After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general industrial or domestic waste.

**LBE2003S
LBE/LCE2009S
LBE/LCE2009SA**

MECHANICAL DATA (continued)

Dimensions in mm

Fig. 1b LCE2009S.

FO-46

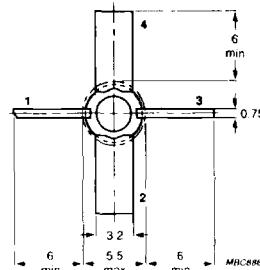
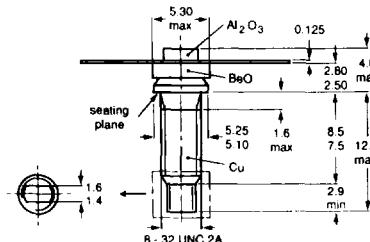
Marking code:

408 = LCE2009S

446 = LCE2009SA

Torque on nut: min. 0.75 Nm
max. 0.85 Nm

Diameter of clearance hole
in heatsink: max. 4.2 mm.



Pinning:

1 = collector

2 = emitter

3 = base

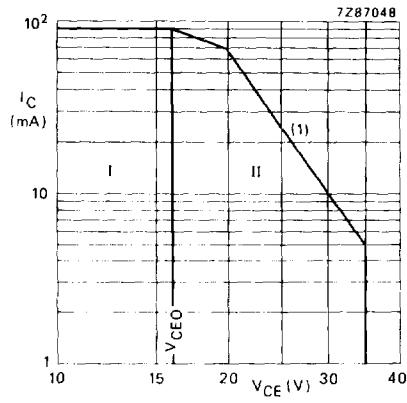
4 = emitter

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

		LBE 2003S	LBE/LCE 2009S	
Collector-base voltage (open emitter)	V _{CBO}	max.	40	40 V
Collector-emitter voltage $R_{BE} = 100 \Omega$	V _{CER}	max.	—	35 V
$R_{BE} = 220 \Omega$	V _{CER}	max.	35	— V
(open base)	V _{CEO}	max.	16	16 V
Emitter-base voltage (open collector)	V _{EBO}	max.	3	3 V
Collector current (DC)	I _C	max.	90	250 mA
Total power dissipation up to $T_{mb} = 75^\circ\text{C}$	P _{tot}	max.	1.4	3.5 W
Storage temperature	T _{stg}		—65 to +150	°C
Operating junction temperature	T _j	max.	200	°C
Lead soldering temperature at 0.3 mm from the case; $t_{sld} = 10 \text{ s}$	T _{sld}	max.	235	°C

LBE2003S



(1) Second breakdown limit
(independent of temperature).

Fig. 2 DC SOAR at $T_{mb} \leq 75$ °C.

I Region of permissible DC operation.

II Permissible extension provided $R_{BE} \leq 220 \Omega$.

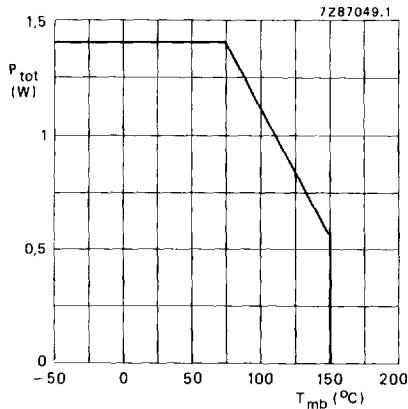
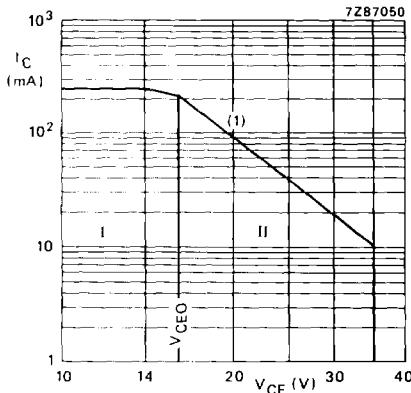


Fig. 3 Power derating curve vs.
mounting base temperature.

LBE/LCE2009S



(1) Second breakdown limit
(independent of temperature).

Fig. 4 DC SOAR at $T_{mb} \leq 75$ °C.

I Region of permissible DC operation.

II Permissible extension provided $R_{BE} \leq 100 \Omega$.

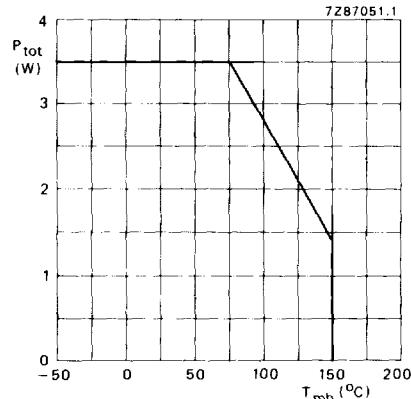


Fig. 5 Power derating curve vs.
mounting base temperature.

LBE2003S
LBE/LCE2009S
LBE/LCE2009SA

THERMAL RESISTANCE (at $T_j = 75^\circ\text{C}$)

	LBE 2003S	LBE/LCE 2009S	
From junction to mounting base	$R_{\text{th j-mb}}$ max.	65	36 K/W*
From mounting base to heatsink	$R_{\text{th mb-h}}$ max.	1.5	1.5 K/W*

CHARACTERISTICS

$T_{\text{mb}} = 25^\circ\text{C}$

	LBE 2003S	LBE/LCE 2009S	
Collector cut-off current $I_E = 0; V_{CB} = 20 \text{ V}$	I_{CBO} <	0.1	0.1 μA
$I_E = 0; V_{CB} = 40 \text{ V}$	I_{CBO} <	150	250 μA
$V_{CB} = 35 \text{ V}; R_{BE} = 220 \Omega$	I_{CER} <	500	— μA
$V_{CB} = 35 \text{ V}; R_{BE} = 100 \Omega$	I_{CER} <	—	1000 μA
Emitter cut-off current $I_C = 0; V_{EB} = 1.5 \text{ V}$	I_{EBO} <	0.05	0.2 μA
DC current gain $I_C = 30 \text{ mA}; V_{CE} = 5 \text{ V}$	h_{FE} > <	15 150	— —
$I_C = 110 \text{ mA}; V_{CE} = 5 \text{ V}$	h_{FE} > <	— —	15 150
Collector-base capacitance at $f = 1 \text{ MHz}$ $I_E = I_C = 0; V_{CB} = 18 \text{ V}; V_{EB} = 1.5 \text{ V}$	C_{cb} typ.	0.3	0.6 pF
Collector-emitter capacitance at $f = 1 \text{ MHz}$ $I_E = I_C = 0; V_{CE} = 18 \text{ V}; V_{EB} = 1.5 \text{ V}$	C_{ce} typ.	0.45	0.6 pF
Emitter-base capacitance at $f = 1 \text{ MHz}$ $I_E = I_C = 0; V_{EB} = 1 \text{ V}; V_{CB} = 10 \text{ V}$	C_{eb} typ.	1.7	3.3 pF

* K/W is SI unit for $^\circ\text{C}/\text{W}$.

s-parameters (common emitter)**LBE2003S:** Typical values; $V_{CE} = 18 \text{ V}^*$; $I_C = 30 \text{ mA}^*$; $T_{mb} = 25^\circ\text{C}$; $Z_0 = 50 \Omega$

f GHz	s _{ie}	s _{re}	s _{fe}	s _{oe}
0,5	0,56/-143°	0,037(-28,6)/ 41°	9,50(19,6)/ 101°	0,56/ -34°
0,6	0,55/-154°	0,040(-28,0)/ 39°	8,28(18,4)/ 93°	0,51/ -35°
0,7	0,55/-164°	0,040(-27,9)/ 40°	7,13(17,1)/ 88°	0,50/ -36°
0,8	0,55/-171°	0,041(-27,7)/ 40°	6,35(16,1)/ 82°	0,49/ -37°
0,9	0,55/-178°	0,043(-27,4)/ 41°	5,69(15,1)/ 77°	0,47/ -38°
1,0	0,55/+176°	0,045(-26,9)/ 40°	5,14(14,2)/ 72°	0,46/ -39°
1,1	0,55/+170°	0,048(-26,4)/ 40°	4,72(13,5)/ 68°	0,46/ -39°
1,2	0,55/+165°	0,051(-25,9)/ 41°	4,37(12,8)/ 64°	0,45/ -41°
1,3	0,56/+159°	0,056(-25,1)/ 41°	4,05(12,2)/ 60°	0,44/ -44°
1,4	0,55/+158°	0,060(-24,5)/ 41°	3,76(11,5)/ 57°	0,45/ -46°
1,5	0,55/+149°	0,062(-24,2)/ 40°	3,52(10,9)/ 53°	0,43/ -48°
1,6	0,55/+146°	0,065(-23,8)/ 42°	3,33(10,5)/ 50°	0,43/ -50°
1,7	0,56/+142°	0,068(-23,3)/ 42°	3,15(10,0)/ 46°	0,43/ -53°
1,8	0,57/+137°	0,070(-23,1)/ 41°	2,96(9,4)/ 42°	0,43/ -54°
1,9	0,57/+132°	0,072(-22,9)/ 40°	2,80(8,9)/ 39°	0,43/ -56°
2,0	0,58/+128°	0,074(-22,7)/ 40°	2,66(8,5)/ 36°	0,42/ -57°
2,2	0,60/+121°	0,081(-21,8)/ 39°	2,43(7,7)/ 28°	0,41/ -61°
2,4	0,62/+114°	0,091(-20,8)/ 37°	2,24(7,0)/ 23°	0,40/ -67°
2,6	0,64/+108°	0,099(-20,1)/ 36°	2,08(6,4)/ 16°	0,39/ -75°
2,8	0,66/+102°	0,105(-19,6)/ 33°	1,90(5,6)/ 10°	0,38/ -82°
3,0	0,68/ +96°	0,108(-19,4)/ 31°	1,79(5,1)/ 4°	0,39/ -87°
3,2	0,71/ +92°	0,124(-18,7)/ 29°	1,63(4,3)/ -2°	0,37/ -94°
3,4	0,73/ +89°	0,125(-18,0)/ 27°	1,58(4,0)/ -7°	0,40/-101°
3,6	0,75/ +86°	0,137(-17,3)/ 25°	1,46(3,3)/ -13°	0,39/-112°
3,8	0,76/ +82°	0,142(-17,0)/ 23°	1,40(2,9)/ -18°	0,38/-120°
4,0	0,77/ +79°	0,149(-16,6)/ 20°	1,31(2,3)/ -24°	0,38/-128°
4,2	0,78/ +75°	0,155(-16,2)/ 17°	1,25(1,9)/ -28°	0,38/-133°
4,4	0,80/ +73°	0,167(-15,5)/ 15°	1,20(1,6)/ -34°	0,39/-142°
4,6	0,81/ +69°	0,177(-15,0)/ 12°	1,14(1,1)/ -38°	0,39/-151°
4,8	0,81/ +68°	0,187(-14,6)/ 10°	1,10(0,8)/ -43°	0,42/-159°
5,0	0,81/ +65°	0,194(-14,3)/ 6°	1,04(0,4)/ -47°	0,44/-165°
5,2	0,80/ +60°	0,203(-13,8)/ 4°	1,03(0,3)/ -53°	0,47/-169°
5,4	0,81/ +56°	0,219(-13,2)/ -1°	0,98(-0,2)/ -57°	0,48/-175°
5,6	0,81/ +51°	0,229(-12,8)/ -3°	0,97(-0,3)/ -62°	0,49/+178°
5,8	0,81/ +48°	0,243(-12,3)/ -8°	0,92(-0,7)/ -68°	0,51/+171°
6,0	0,80/ +44°	0,245(-12,2)/ -12°	0,90(-0,9)/ -72°	0,55/+165°

The figures given between brackets are values in dB.

* V_{CE} and I_C regulated.

LBE 2003S
LBE/LCE2009S
LBE/LCE2009SA

s-parameters (common emitter)

LBE/LCE2009S: Typical values; $V_{CE} = 18 \text{ V}^*$; $I_C = 110 \text{ mA}^*$; $T_{mb} = 25^\circ\text{C}$; $Z_0 = 50 \Omega$

f GHz	s _{ie}	s _{re}	s _{fe}	s _{oe}
0,5	0,70/177°	0,029(-30,7)/50°	7,55(17,6)/ 83°	0,25/-48°
0,6	0,70/171°	0,033(-29,6)/51°	6,43(16,2)/ 77°	0,22/-50°
0,7	0,70/168°	0,036(-29,0)/53°	5,46(14,6)/ 73°	0,23/-52°
0,8	0,70/163°	0,039(-28,4)/54°	4,80(13,6)/ 68°	0,22/-54°
0,9	0,71/159°	0,041(-27,8)/54°	4,27(12,6)/ 64°	0,22/-56°
1,0	0,71/155°	0,045(-27,0)/55°	3,84(11,7)/ 60°	0,21/-59°
1,1	0,71/151°	0,049(-26,2)/54°	3,53(11,0)/ 56°	0,21/-62°
1,2	0,71/148°	0,054(-25,4)/54°	3,27(10,3)/ 52°	0,21/-65°
1,3	0,71/144°	0,060(-24,5)/53°	3,01(9,6)/ 48°	0,20/-74°
1,4	0,72/143°	0,066(-23,6)/54°	2,80(9,0)/ 45°	0,20/-79°
1,5	0,72/136°	0,070(-23,1)/52°	2,61(8,3)/ 41°	0,21/-80°
1,6	0,72/133°	0,075(-22,5)/53°	2,47(7,9)/ 38°	0,21/-83°
1,7	0,72/130°	0,080(-21,9)/51°	2,33(7,3)/ 34°	0,22/-87°
1,8	0,73/127°	0,084(-21,5)/49°	2,18(6,8)/ 30°	0,22/-90°
1,9	0,73/123°	0,087(-21,2)/48°	2,05(6,3)/ 26°	0,22/-94°
2,0	0,74/120°	0,090(-20,9)/46°	1,97(5,9)/ 23°	0,22/-97°
2,2	0,75/114°	0,100(-20,0)/43°	1,78(5,0)/ 15°	0,22/-109°
2,4	0,77/108°	0,112(-19,0)/40°	1,63(4,3)/ 10°	0,21/-122°
2,6	0,79/103°	0,123(-18,2)/37°	1,51(3,6)/ 2°	0,24/-133°
2,8	0,80/ 97°	0,129(-17,8)/33°	1,36(2,7)/ -4°	0,25/-143°
3,0	0,81/ 92°	0,134(-17,5)/30°	1,28(2,1)/-11°	0,27/-151°
3,2	0,83/ 88°	0,143(-16,9)/26°	1,15(1,2)/-17°	0,28/-163°
3,4	0,85/ 85°	0,152(-16,4)/24°	1,10(0,9)/-21°	0,30/-173°
3,6	0,86/ 82°	0,163(-15,8)/20°	1,00(0)/-28°	0,34/+178°
3,8	0,87/ 79°	0,168(-15,5)/17°	0,96(-0,4)/-32°	0,37/+173°
4,0	0,88/ 75°	0,175(-15,2)/14°	0,88(-1,1)/-39°	0,41/+168°
4,2	0,88/ 71°	0,180(-14,9)/11°	0,83(-1,6)/-42°	0,42/+162°
4,4	0,89/ 69°	0,193(-14,3)/ 8°	0,79(-2,1)/-48°	0,45/+155°
4,6	0,90/ 66°	0,200(-14,0)/ 5°	0,74(-2,6)/-51°	0,48/+149°
4,8	0,90/ 64°	0,211(-13,5)/ 2°	0,71(-3,0)/-56°	0,52/+145°
5,0	0,90/ 61°	0,214(-13,4)/-2°	0,66(-3,6)/-59°	0,55/+144°

The figures given between brackets are values in dB.

* V_{CE} and I_C regulated.

APPLICATION INFORMATION

Microwave performance in CW operation for the **LBE 2003S** up to $T_{mb} = 25^{\circ}\text{C}$ in a common-emitter class-A circuit*

f GHz	V_{CE} (1) V	I_C (1) mA	P_{L1} (2) mW(dBm)	G_{po} (3) dB	z_i Ω	Z_L Ω
2	18	30	$\geq 200(23)$ typ. 250(24)	≥ 10 typ. 11	$6.2 + j30$	$17.5 + j7$

Notes

1. V_{CE} and I_C regulated.
2. Load power for 1 dB compressed power gain.
3. Low-level power gain associated with P_{L1} .

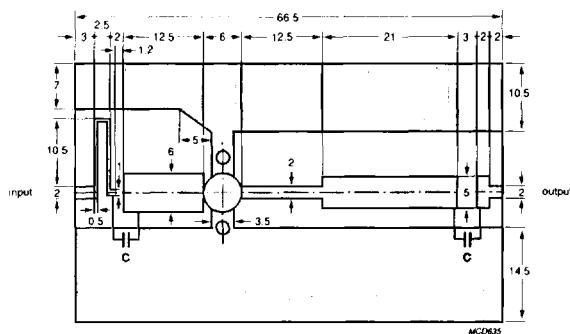


Fig. 6 Prematching test circuit board for 2 GHz. (Dimensions in mm.)

Striplines on a double Cu-clad printed-circuit board with PTFE fibre-glass dielectric ($\epsilon_r \approx 2.54$); thickness 0.8 mm.

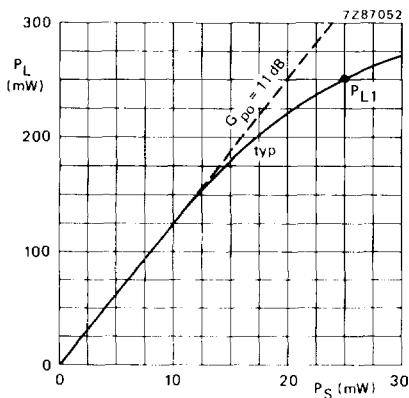


Fig. 7 $V_{CE} = 18$ V; $I_C = 30$ mA;
 $f = 2$ GHz; $T_{mb} = 25^{\circ}\text{C}$.

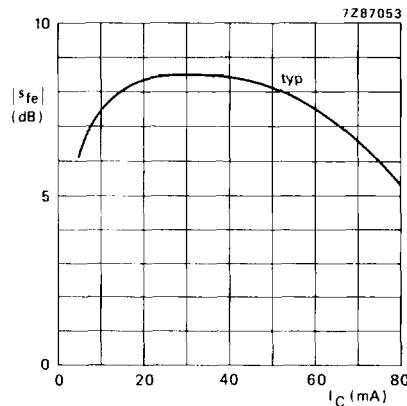


Fig. 8 $V_{CE} = 18$ V; class-A
operation; $f = 2$ GHz; $T_{mb} = 25^{\circ}\text{C}$.

* Circuit consists of prematching circuit board in combination with input and output slug tuners.

APPLICATION INFORMATION

Microwave performance in CW operation for the **LBE/LCE2009S** up to $T_{mb} = 75^{\circ}\text{C}$ in a common-emitter class-A circuit*

f GHz	V_{CE} (1) V	I_C (1) mA	P_{L1} (2) mW(dBm)	G_{po} (3) dB	z_i Ω	Z_L Ω
2	18	100	$\geq 700(28.5)$ typ. 900(29.5)	≥ 9 typ. 9.8	$7.5 + j14.5$	$17.5 + j38.5$

Notes

1. V_{CE} and I_C regulated.
2. Load power for 1 dB compressed power gain.
3. Low-level power gain associated with P_{L1} .

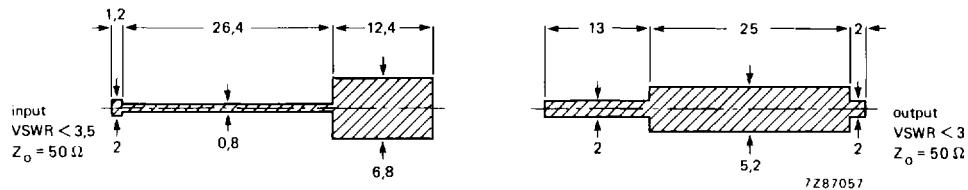


Fig. 9 Prematching test circuit board for 2 GHz. (Dimensions in mm.)

Striplines on a double Cu-clad printed-circuit board with PTFE fibre-glass dielectric ($\epsilon_r \approx 2.54$); thickness 0.8 mm.

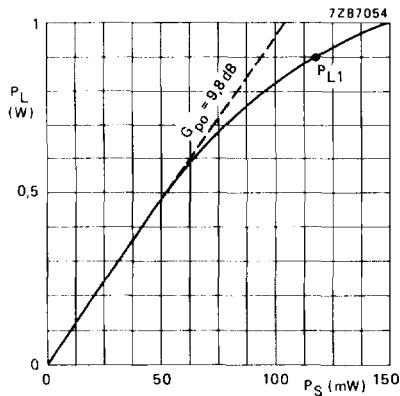


Fig. 10 $V_{CE} = 18$ V; $I_C = 110$ mA;
 $f = 2$ GHz; $T_{mb} = 25^{\circ}\text{C}$.

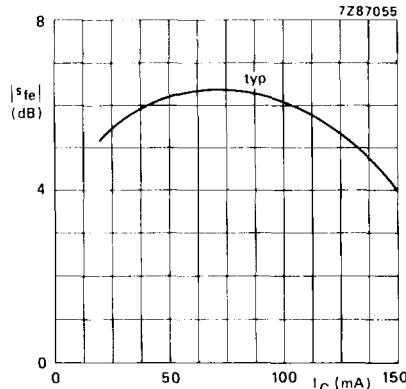


Fig. 11 $V_{CE} = 18$ V; class-A
operation; $f = 2$ GHz; $T_{mb} = 25^{\circ}\text{C}$.

* Circuit consists of prematching circuit board in combination with input and output slug tuners.